

FL660N-03-50

High Power type LED

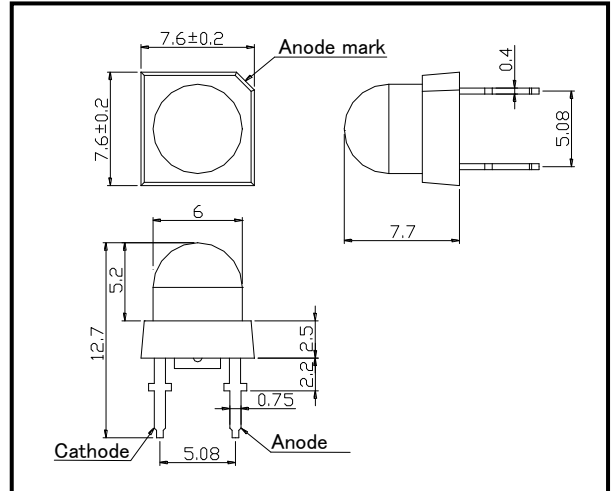
FL660N-03-50 is an AlGaInP LED mounted on a lead frame and molded with super beam lens. On forward bias, it emits a band of visible light which peaks 660nm.

These devices are intended to be operated at pulsed current of 500mA under maximum 4V

◆ Specifications

- 1) Product Name Super Flux mold type LED
- 2) Type No. FL660N-03-50
- 3) Chip
 - (1) Chip Material AlGaInP
 - (2) Chip Dimension 500um*500um
 - (3) Peak Wavelength 660nm typ.
- 4) Package
 - (1) Type Super Beam type LED
 - (2) Resin Material Epoxy Resin
 - (3) Lead Frame Silver Plated Copper

◆ Outer dimension (Unit: mm)



◆ Absolute Maximum Ratings

Item	Symbol	Maximum Rated Value	Unit	Ambient Temperature
Power Dissipation	P _D	390	mW	T _a =25°C
Forward Current	I _F	150	mA	T _a =25°C
Pulse Forward Current	I _{FP}	500	mA	T _a =25°C
Reverse Voltage	V _R	10	V	T _a =25°C
Thermal Resistance	R _{thja}	100	K/W	
Operating Temperature	T _{OPR}	-30 ~ +85	°C	
Storage Temperature	T _{STG}	-40 ~ +100	°C	
Soldering Temperature	T _{SOL}	265	°C	

‡Pulse Forward Current condition: Duty=1% and Pulse Width=10us.

‡Soldering condition: Soldering condition must be completed within 3 seconds at 265°C

◆ Electro-Optical Characteristics [T_a=25°C]

Item	Symbol	Condition	Minimum	Typical	Maximum	Unit
Forward Voltage	V _F	I _F =100mA		2.2	2.5	V
Pulsed Forward Voltage	V _F	I _{FP} =500mA		3.0	4.0	V
Reverse Current	I _R	V _R =10V			10	uA
Radiated Power	P _O	I _F =100mA	40	70		mW
Radiant Intensity	I _E	I _F =100mA		190		mW/sr
Brightness	I _v	I _F =100mA		18000		mcd
Peak Wavelength	λ _P	I _F =100mA	650	660	670	nm
Half Width	Δλ	I _F =100mA		18		nm
Viewing Half Angle	θ _{1/2}	I _F =100mA		±9		deg.
Rise Time	t _r	I _F =100mA		60		ns
Fall Time	t _f	I _F =100mA		6		ns

‡Radiated Power is measured by S3584-08.

‡Radiant Intensity is measured by Tektronix J-6512.